

Silicon NPN Power Transistors

BU2722AF

DESCRIPTION

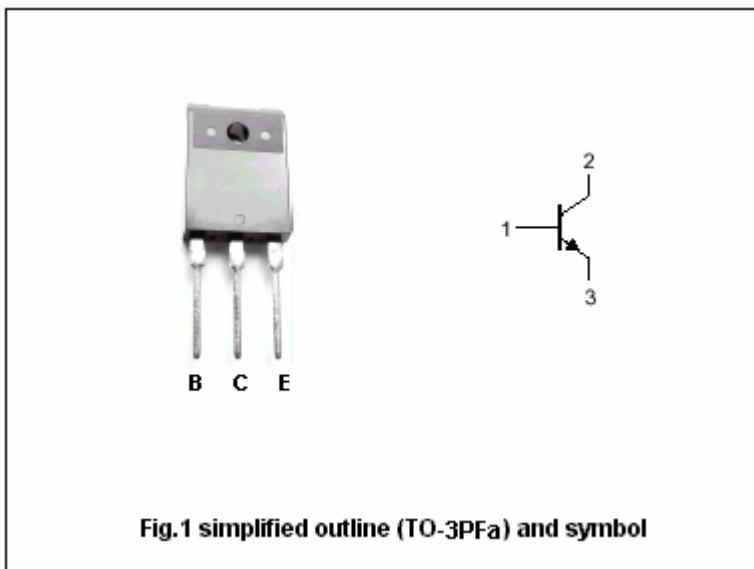
- With TO-3PFa package
- High voltage
- High speed switching

APPLICATIONS

- For use in horizontal deflection circuits of high resolution monitors

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |



Absolute maximum ratings(Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|---------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 1700 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 825 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 7.5 | V |
| I _C | Collector current (DC) | | 10 | A |
| I _{CM} | Collector current-peak | | 25 | A |
| I _B | Base current (DC) | | 10 | A |
| I _{BM} | Base current-peak | | 14 | A |
| P _T | Total power dissipation | T _C =25°C | 45 | W |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -65~150 | °C |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|------------|------|
| V _{CEO(SUS)} | Collector-emitter sustaining voltage | I _C =100mA ; I _B =0, L=25mH | 825 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =1mA ; I _C =0 | 7.5 | 13.5 | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =4.5A ; I _B =1.0A | | | 1.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =4.5A ; I _B =1.0A | | | 1.0 | V |
| I _{CES} | Collector cut-off current | V _{CE} =BV _{CES} ; V _{BE} =0 T _j =125 °C | | | 1.0 2.0 | mA |
| I _{EBO} | Emitter cut-off current | V _{EB} =7.5V; I _C =0 | | | 1.0 | mA |
| h _{FE-1} | DC current gain | I _C =0.1A ; V _{CE} =5V | | 22 | | |
| h _{FE-2} | DC current gain | I _C =4.5A ; V _{CE} =1V | 4.5 | | 10 | |

